Journal of Crystal Growth 102 (1990) 1075–1081
North-Holland

AUTHOR INDEX

Agnello, P.D., P.B. Chinoy and S.K. Ghandhi, A study of indium depletion in the OMVPE growth of GaInAs 102 (1990) 775
Alnot, M., J.A. Barnard, J.J. Ehrhardt and B. Mutaftschiev, Growth kinetics of the Pt(111) surface during low temperature vacuum deposition 102 (1990) 629
Ard, C.K., see Nouruzi-Khorasani 102 (1990) 819
Ard, C.K., see Capper 102 (1990) 848
Armelles, G., see Vazquez 102 (1990) 891
Astles, M.G., see Nouruzi-Khorasani 102 (1990) 819
Astles, M.G., see Nouruzi-Khorasani 102 (1990) 1069
Auvray, P., M. Baudet, A. Poudoulec, C. Guillemot and A. Regreny, The use of superlattices as internal standards for composition and thickness measurements in modulation-doped quantum well structures 102 (1990) 939

Balk, P., see Frese 102 (1990) 290
Barnard, J.A., see Alnot 102 (1990) 629
Barns, R.L., see Laudise 102 (1990) 21
Baudet, M., see Auvray 102 (1990) 939
Bauer, G., see Clemens 102 (1990) 933
Beiny, D.H.M., J.W. Mullin and K. Lewtas, Crystallization of n-dotriacontane from hydrocarbon solution with polymeric additives 102 (1990) 801
Belt, R.F., see Laudise 102 (1990) 427
Benakki, S., see Wu 102 (1990) 701
Bennema, P., see Bolt 102 (1990) 329
Bennema, P. and O. Söhnel, Interfacial surface tension for crystallization and precipitation from aqueous solutions 102 (1990) 547
Benyon, W., see Knight 102 (1990) 249
Berglund, K.A., see Cerreta 102 (1990) 869
Bevan, M.J., N.J. Doyle and D. Snyder, A comparison of $Hg_{1-x}Cd_xTe$ MOCVD films on lattice-matched (CdZn)Te and Cd(TeSe) substrates 102 (1990) 785
Bhat, I.B., see Parat 102 (1990) 413
Bhat, R., see Caneau 102 (1990) 491
Black, S.N., see Davey 102 (1990) 97
Böhm, H., see Oesten 102 (1990) 919
Boistelle, R. and I. Lopez-Valero, Growth units and nucleation: the case of calcium phosphates 102 (1990) 609
Bolt, R.J. and P. Bennema, Potassium titanyl phosphate $KTiOPO_4$ (KTP): relation between crystal structure and morphology 102 (1990) 329
Böttner, H., see Clemens 102 (1990) 933
Bourret, E.D., J.B. Guitron, M.L. Galiano and E.E. Haller, Vertical seeded melt growth of GaAs 102 (1990) 877
Bozovic, I., see Schlom 102 (1990) 361
Brauers, A., see Frese 102 (1990) 290
Bravman, J.C., see Schlom 102 (1990) 361
Briggs, A.T.R., see Butler 102 (1990) 393
Briones, F., see Vazquez 102 (1990) 891
Brown, D.W., see Larsen 102 (1990) 126
Brown, P.D., see Loginov 102 (1990) 827
Bruines, J.J.P., J. Le Bris, M. Renaud and M. Erman, Spatially-resolved photoluminescence study of InP:Fe substrates from different suppliers 102 (1990) 769
Brush, L.N., S.R. Coriell and G.B. McFadden, Directional solidification of a planar interface in the presence of a time-dependent electric current 102 (1990) 725
Buchan, N.I., see Larsen 102 (1990) 103
Buchan, N.I., see Larsen 102 (1990) 126
Butler, B.R., A.T.R. Briggs, S.A. Kitching and A. Chew, Hydrogen passivation during cooling of p-type InP grown by metal-organic vapour phase epitaxy, due to a combined reaction between phosphine and dimethylzinc 102 (1990) 393

Caneau, C., H.J. Yoo, R. Bhat, M. Koza and J.R. Hayes, Selective in situ etching of GaInAsP for improved growth interfaces 102 (1990) 491
Capper, P., W.G. Coates, C.L. Jones, J.J.G. Gosney, I. Kenworthy and C.K. Ard, Effect of process changes on the properties of $Cd_xHg_{1-x}Te$ crystals grown by Bridgman using ACRT 102 (1990) 848
Carlson, D.J., see Laudise 102 (1990) 21
Caulet, J., A. Le Corre, B. Guenais, G. Ropars and A. Guivarc'h, Molecular beam epitaxial growth of lattice matched GaAs/$ErP_{0.6}As_{0.4}$/(001) and (111) GaAs heterostructures 102 (1990) 309
Caulet, J., see Guenais 102 (1990) 925
Cerreta, M.K. and K.A. Berglund, Contact nuclei formation in aqueous dextrose solutions 102 (1990) 869
Chang, C.Y., see Lin 102 (1990) 354
Chełkowski, A., see Majewska 102 (1990) 187

Chen, R.-C., G. Fornuto, C. Lamberti and S. Pellegrino, Growth of high purity InGaAs LPE layers and their characterization 102 (1990) 477
Chen, Z.J., see Schlom 102 (1990) 361
Chernov, A.A., see Vekilov 102 (1990) 706
Chernov, A.A., N.P. Zaitseva and L.N. Rashkovich, Secondary nucleation induced by the cracking of a growing crystal: KH_2PO_4 (KDP) and $K(H,D)_2PO_4$ (DKDP) 102 (1990) 793
Chew, A., see Butler 102 (1990) 393
Chinoy, P.B., see Agnello 102 (1990) 775
Christoffel, E., see Wu 102 (1990) 701
Chu, H.C., see Lin 102 (1990) 354
Clemens, H., A. Voiticek, A. Holzinger, G. Bauer and H. Böttner, Influence of the BaF_2 substrate preparation on the structural perfection of epitaxially grown IV–VI compounds 102 (1990) 933
Coates, W.G., see Nouruzi-Khorasani 102 (1990) 819
Coates, W.G., see Capper 102 (1990) 848
Coriell, S.R., see Brush 102 (1990) 725

Daams, J.L.C., see Haisma 102 (1990) 1014
Daly, J., see Dilawari 102 (1990) 635
Davey, R.J., S.N. Black, L.J. Williams, D. McEwan and D.E. Sadler, The chiral purity of a triazolylketone crystallised from racemic solutions 102 (1990) 97
De Croon, M.H.J.M., see Van Sark 102 (1990) 1
De Croon, M.H.J.M., see Gardeniers 102 (1990) 233
De Jong, A.F., see Haisma 102 (1990) 1014
De Melo, O., O. Ori and C. Pelosi, The application of the Bragg–Williams model to the description of fundamental thermodynamical properties of binary semiconducting compounds 102 (1990) 141
De Miguel, J.L., see Vazquez 102 (1990) 891
Desai, C.C. and M.S.V. Ramana, Nucleation density and electrolytic growth of lead hydrogen phosphate single crystals in silica gels 102 (1990) 191
Devenyns, J.A.H., see Verbeeck 102 (1990) 647
Dilawari, A.H., J. Szekely and J. Daly, Experimental measurements and theoretical predictions for the MOCVD of gallium arsenide using a barrel-type reactor 102 (1990) 635
Ditchek, B.M., J. Hefter, T.R. Middleton and J. Pelleg, Microstructure of Czochralski-grown Si–$TaSi_2$ eutectic composites 102 (1990) 401
Dobson, P.S., see Nouruzi-Khorasani 102 (1990) 819
Dobson, P.S., see Nouruzi-Khorasani 102 (1990) 1069
Doyle, N.J., see Bevan 102 (1990) 785
Draeger, N.A., Codeposition of aluminum oxide and silicon oxide on a single crystal tungsten surface 102 (1990) 908

Eckold, G., see Sonntag 102 (1990) 957
Eckstein, J.N., see Schlom 102 (1990) 361
Eguchi, M., see Kakimoto 102 (1990) 16
Ehrhardt, J.J., see Alnot 102 (1990) 629
Erman, M., see Bruines 102 (1990) 769
Etem, Y., see Nouruzi-Khorasani 102 (1990) 819
Etgens, V.H., see Jedrecy 102 (1990) 293

Fang, Y.K., see Lin 102 (1990) 354
Fedorov, O.P., Interaction between growing crystals and inclusions in the melt 102 (1990) 857
Feigelson, R.S., see Lu 102 (1990) 807
Fornuto, G., see Chen 102 (1990) 477
Fotiadis, D.I., S. Kieda and K.F. Jensen, Transport phenomena in vertical reactors for metalorganic vapor phase epitaxy. I. Effects of heat transfer characteristics, reactor geometry, and operating conditions 102 (1990) 441
Fotiadis, D.I. and K.F. Jensen, Thermophoresis of solid particles in horizontal chemical vapor deposition reactors 102 (1990) 743
Fraundorf, G.K. and L. Shive, Transmission electron microscope study of quartz crucibles used in growth of Czochralski silicon 102 (1990) 157
Frese, V., G.K. Regel, H. Hardtdegen, A. Brauers, P. Balk, M. Hostalek, M. Lokai and L. Pohl, Coordinatively saturated Ga compounds – a new type of group III precursor for the MOCVD of GaAs 102 (1990) 290
Furuhata, N., A. Okamoto and H. Hoshino, High purity GaAs and $Al_xGa_{1-x}As$ grown by metalorganic molecular beam epitaxy 102 (1990) 814

Gadkari, S.C., K.P. Muthe, K.D. Singh, S.C. Sabharwal and M.K. Gupta, Growth of single crystals in $Bi_2(Sr,Ca)_{n+1}Cu_nO_x$ system 102 (1990) 685
Galiano, M.L., see Bourret 102 (1990) 877
Gao, Y., see Molassioti 102 (1990) 974
Gardeniers, J.G.E., M.M.W. Mooren, M.H.J.M. de Croon and L.J. Gilling, The influence of the chlorine–hydrogen ratio in the gas phase on the stability of the {113} faces of silicon in Si–H–Cl CVD 102 (1990) 233
Gashurov, G., see Laudise 102 (1990) 427
Ghandhi, S.K., see Parat 102 (1990) 413
Ghandhi, S.K., see Agnello 102 (1990) 775
Giling, L.J., see Van Sark 102 (1990) 1
Giling, L.J., see Gardeniers 102 (1990) 233
Giling, L.J., see Visser 102 (1990) 529
Giling, L.J., see Keizer 102 (1990) 667
Gillot, B., see Viale 102 (1990) 269
Glaser, R., see Zundelevich 102 (1990) 69
Goltzene, A., see Wu 102 (1990) 701
Gon, H.B., Ferroelectricity in calcium tartrate single crystals grown by gel technique 102 (1990) 501

Gonda, T., H. Kakiuchi and K. Moriya, In situ observation of internal structure in growing ice crystals by laser scattering tomography 102 (1990) 167
Gonzalez, L., see Vazquez 102 (1990) 891
Gosney, J.J.G., see Capper 102 (1990) 848
Gouzerh, J., see Gouzerh 102 (1990) 1059
Gouzerh, P., F. Robert, J. Gouzerh and H. Makram, The effect of the oxygen pressure on the growth of single crystals of $YBa_2Cu_3O_{7-x}$ and $Y_{0.8}Ba_{1.2}Cu_{0.15}Pt_{0.9}O_6$ 102 (1990) 1059
Govers, C.A.M., see Visser 102 (1990) 529
Greiser, N., see Jedrecy 102 (1990) 293
Gualtieri, G.J., see Schwartz 102 (1990) 147
Guan Weiyan, see Ren 102 (1990) 349
Guenais, B., see Caulet 102 (1990) 309
Guenais, B., A. Poudoulec, J. Caulet and A. Guivarc'h, Vacuum stability of epitaxial NiGa and Ni_2Ga_3 layers MBE grown onto a GaAs substrate 102 (1990) 925
Guillemot, C., see Auvray 102 (1990) 939
Guitron, J.B., see Bourret 102 (1990) 877
Guivarc'h, A., see Caulet 102 (1990) 309
Guivarc'h, A., see Guenais 102 (1990) 925
Gupta, M.K., see Gadkari 102 (1990) 685

Haga, T., see Hiruma 102 (1990) 717
Haisma, J., J.A. Pistorius and D. Mateika, Lattice-constant-adaptable crystallographics. I. Heteroepitaxial growth of semiconductors and other specific compounds on lattice-constant-adapted garnets, spinels and perovskites; a systematic geometrical (not experimental) evaluation 102 (1990) 979
Haisma, J., see Mateika 102 (1990) 994
Haisma, J., J.L.C. Daams, A.F. de Jong, B.H. Koek, J.W.F. Maes, D. Mateika, J.A. Pistorius and P.J. Roksnoer, Lattice-constant-adaptable crystallographics. III. Heteroepitaxial phenomena of semiconductors on garnets; an experimental verification 102 (1990) 1014
Haller, E.E., see Bourret 102 (1990) 877
Hamabe, T., see Kitano 102 (1990) 965
Hamza, S.M., The influence of some metal ions on the kinetics of dissolution of barium fluoride 102 (1990) 303
Hardtdegen, H., see Frese 102 (1990) 290
Harris, Jr., J.S., see Schlom 102 (1990) 361
Hart, J.E., see Pratte 102 (1990) 54
Hasegawa, F., see Kobayashi 102 (1990) 471
Hayes, J.R., see Caneau 102 (1990) 491
He Youping, see Huang 102 (1990) 762
Hefter, J., see Ditchek 102 (1990) 401
Herz, K., see Sonntag 102 (1990) 957
Heyraud, J.C., see Wynblatt 102 (1990) 618
Hibiya, T., see Kakimoto 102 (1990) 16
Hibiya, T., S. Imoto, T. Satoh, Y. Nakabayashi and M. Sakonjyu, Single crystal growth of $Pb_2YBa_2Cu_3O_8$ and $YBa_2Cu_3O_{1-x}$ from $PbO-B_2O_3$ melts 102 (1990) 862
Hinz, B., see Roy 102 (1990) 1061
Hiruma, K., T. Haga and M. Miyazaki, Surface migration and reaction mechanism during selective growth of GaAs and AlAs by metalorganic chemical vapor deposition 102 (1990) 717
Hodorowicz, S.A., see Olech 102 (1990) 562
Hogenkamp, J.E.M., see Van Sark 102 (1990) 1
Hohlwein, D., see Sonntag 102 (1990) 957
Holzinger, A., see Clemens 102 (1990) 933
Hoshino, H., see Furuhata 102 (1990) 814
Hostalek, M., see Frese 102 (1990) 290
Huang Bingrong, Su Genbo and He Youping, Growth of large size urea crystals 102 (1990) 762

Iida, J., S. Takekawa and N. Kimizuka, Single crystal growth of $LuFe_2O_4$, $LuFeCoO_4$ and $YbFeMgO_4$ by the floating zone method 102 (1990) 398
Imoto, S., see Hibiya 102 (1990) 862
Inada, T., see Shibata 102 (1990) 557
Inada, T., Y. Otoki and S. Kuma, Quasi-quantitative estimation of solidus curve on As-rich side of Ga–As system 102 (1990) 915
Inoue, N., see Kobayashi 102 (1990) 183
Isshiki, M., M. Piechotka and E. Kaldis, Vapor growth kinetics of α-HgI_2 crystals 102 (1990) 344

Jedrecy, N., M. Sauvage-Simkin, R. Pinchaux, J. Massies, N. Greiser and V.H. Etgens, Misfit evolution in the early stages of the heteroepitaxial growth of GaAs on Si(001): an in-situ X-ray scattering study 102 (1990) 293
Jenkins, D.R., Oscillatory instability in a model of directional solidification 102 (1990) 481
Jensen, K.F., see Fotiadis 102 (1990) 441
Jensen, K.F., see Fotiadis 102 (1990) 743
Jia Shouquan, see Wang 102 (1990) 678
Jiang, M.H., see Zhang 102 (1990) 581
Jiang Yandao, see Ren 102 (1990) 349
Jin, Y., see Kobayashi 102 (1990) 471
Jingping, Zhang, see Tang 102 (1990) 681
Jones, C.L., see Capper 102 (1990) 848
Jones, I.P., see Nouruzi-Khorasani 102 (1990) 819
Jones, I.P., see Nouruzi-Khorasani 102 (1990) 1069
Jurisch, M. and W. Löser, Analysis of periodic non-rotational W striations in Mo single crystals due to nonsteady thermocapillary convection 102 (1990) 214
Jurisch, M., Surface temperature oscillations of a floating zone resulting from oscilatory thermocapillary convection 102 (1990) 223

Kakimoto, K., M. Eguchi, H. Watanabe and T. Hibiya, Flow instability of molten silicon in the Czochralski configuration 102 (1990) 16
Kakiuchi, H., see Gonda 102 (1990) 167
Kaldis, E., see Isshiki 102 (1990) 344
Kammlott, G.W., see Laudise 102 (1990) 21
Kanaya, Y., see Tanako 102 (1990) 341
Kawachi, M., see Terashima 102 (1990) 387
Keizer, L.C., X. Tang, R.Z.C. van Meerten and L.J. Giling, Doping of gallium arsenide in MOCVD: equilibrium calculations 102 (1990) 667
Kelly, F.X. and L.H. Ungar, A molecular dynamics investigation of solute trapping during rapid solidification of silicon 102 (1990) 658
Kenworthy, I., see Capper 102 (1990) 848
Kieda, S., see Fotiadis 102 (1990) 441
Kikuta, T., see Yoshida 102 (1990) 696
Kimizuka, N., see Iida 102 (1990) 398
Kitamura, M., Precipitation mechanism of polymorphous clathrate crystals of Ni-complex at high concentrations of 1-methylnaphthalene 102 (1990) 255
Kitano, M., T. Hamabe, S. Maeda and T. Okabe, Growth of large tetrapod-like ZnO crystals. I. Experimental considerations on kinetics of growth 102 (1990) 965
Kitching, S.A., see Butler 102 (1990) 393
Knight, D.G. and W. Benyon, Method for reliable liquid phase epitaxial growth of semi-insulating InP doped with Ti and Zn 102 (1990) 249
Kobayashi, M., see Yoshimura 102 (1990) 1035
Kobayashi, R., H. Yamaguchi, Y. Jin and F. Hasegawa, Difference of reaction between AsH_3 and arsenic vapor from As metal in vapor phase epitaxy of GaAs 102 (1990) 471
Kobayashi, T. and N. Inoue, Carbon-doped GaAs grown by metalorganic vapor phase epitaxy using TMAs and TEG 102 (1990) 183
Koek, B.H., see Haisma 102 (1990) 1014
Koide, Y.S. Zaima, N. Ohshima and Y. Yasuda, Growth processes in the initial stages of deposition of Ge films on (100)Si surfaces by GeH_4 source molecular beam epitaxy (E) 102 (1990) 690
Komatsu, S. and Y. Moriyoshi, Growth of boron whiskers and ribbons in a low-pressure $B_2H_6 + He + H_2$ plasma 102 (1990) 899
Kopetsch, H., Numerical simulation of the interface inversion in Czochralski growth of oxide crystals 102 (1990) 505
Kou, S., see Lan 102 (1990) 1043
Koza, M., see Caneau 102 (1990) 491
Kubota, N., T. Sekimoto and K. Shimizu, Precipitation of $BaCO_3$ in a semi-batch reactor with double-tube gas injection nozzle 102 (1990) 434
Kuma, S., see Shibata 102 (1990) 557
Kuma, S., see Inada 102 (1990) 915
Kung, J.H., see Lin 102 (1990) 354
Kunii, Y., see Ueno 102 (1990) 643
Kuznetzov, Yu.G., see Vekilov 102 (1990) 706

Lamberti, C., see Chen 102 (1990) 477
Lan, C.W. and S. Kou, Thermocapillary flow and melt/solid interfaces in floating-zone crystal growth under microgravity 102 (1990) 1043
Larsen, C.A., N.I. Buchan, S.H. Li and G.B. Stringfellow, Decomposition mechanisms of trimethylgallium 102 (1990) 103
Larsen, C.A., see Li 102 (1990) 117
Larsen, C.A., S.H. Li, N.I. Buchan, G.B. Stringfellow and D.W. Brown, Kinetics of the reaction between trimethylgallium and arsine 102 (1990) 126
Laudise, R.A., W.A. Sunder, R.L. Barns, G.W. Kammlott, A.F. Witt and D.J. Carlson, Czochralski crystal growth in the system $PtMn_xSb_{2-x}$ 102 (1990) 21
Laudise, R.A., W.A. Sunder, R.F. Belt and G. Gashurov, Solubility and $P-V-T$ relations and the growth of potassium titanyl phosphate 102 (1990) 427
Le Bris, J., see Bruines 102 (1990) 769
Le Corre, A., see Caulet 102 (1990) 309
Lee, C.H., see Wu 102 (1990) 701
Lee, D.D., The structure and mechanism of growth of calcium carbonate minerals in early stages of shells of the oyster *Crassostrea virginica* 102 (1990) 262
Leonov, A.G., see Satunkin 102 (1990) 592
Lewtas, K., see Beiny 102 (1990) 801
Li, S.H., see Larsen 102 (1990) 103
Li, S.H., C.A. Larsen and G.B. Stringfellow, Decomposition mechanisms of trimethylarsine 102 (1990) 117
Li, S.H., see Larsen 102 (1990) 126
Lin, W.T., H.C. Chu, Y.K. Fang, C.Y. Chang, P.T. Wu and J.H. Kung, Phase transformation in Bi–Ca–Sr–Cu–O thin films 102 (1990) 354
Loginov, Y.Y., P.D. Brown, N. Thompson, G.J. Russell and J. Woods, TEM investigation of Ga and In doped ZnS, and In doped ZnSe 102 (1990) 827
Lokai, M., see Frese 102 (1990) 290
Lopez-Valero, I., see Boistelle 102 (1990) 609
Löser, W., see Jurisch 102 (1990) 214
Lu, Y.-C., J.-J. Shiau, R.S. Feigelson and R.K. Route, Effect of vibrational stirring on the quality of Bridgman-grown CdTe 102 (1990) 807
Lunn, M.A., see Nouruzi-Khorasani 102 (1990) 1069
Luo, Zundu, see Wang 102 (1990) 765

Maeda, S., see Kitano 102 (1990) 965
Maes, J.W.F., see Haisma 102 (1990) 1014

Maiwa, K., K. Tsukamoto and I. Sunagawa, Activities of spiral growth hillocks on the (111) faces of barium nitrate crystals growing in an aqueous solution 102 (1990) 43
Makram, H., see Gouzerh 102 (1990) 1059
Marshall, A.F., see Schlom 102 (1990) 361
Massies, J., see Jedrecy 102 (1990) 293
Mateika, D., see Haisma 102 (1990) 979
Mateika, D., E. Völkel and J. Haisma, Lattice-constant-adaptable crystallographics. II. Czochralski growth from multicomponent melts of homogeneous mixed-garnet crystals 102 (1990) 994
Mateika, D., see Haisma 102 (1990) 1014
Matsumoto, K. and K. Noda, Crystal growth of ZnO by chemical transport using $HgCl_2$ as a transport agent 102 (1990) 137
Matsunami, H., see Ozasa 102 (1990) 31
McEwan, D., see Davey 102 (1990) 97
McFadden, G.B., see Brush 102 (1990) 725
Melikhov, I.V. and A. Pamiatnikh, Dendrite relay crystallization of the dispersed melt 102 (1990) 885
Mersmann, A., Calculation of interfacial tensions 102 (1990) 841
Métois, J.J., see Wynblatt 102 (1990) 618
Middleton, T.R., see Ditchek 102 (1990) 401
Miyazaki, M., see Hiruma 102 (1990) 717
Mo, P.G., see Wu 102 (1990) 701
Molassioti, A., F. Scholz and Y. Gao, Zinc doping in InP grown by atmospheric pressure metalorganic vapor phase epitaxy 102 (1990) 974
Mooren, M.M.W., see Gardeniers 102 (1990) 233
Moriya, K., see Gonda 102 (1990) 167
Moriyoshi, Y., see Komatsu 102 (1990) 899
Motakef, S., Interference of buoyancy-induced convection with segregation during directional solidification: scaling laws 102 (1990) 197
Müller, I., see Roy 102 (1990) 1061
Mullin, J.W., see Beiny 102 (1990) 801
Mutaftschiev, B., see Alnot 102 (1990) 629
Muthe, K.P., see Gadkari 102 (1990) 685

Nakabayashi, Y., see Hibiya 102 (1990) 862
Nakayama, M., see Yoshida 102 (1990) 696
Noda, K., see Matsumoto 102 (1990) 137
Nonaka, K., see Yoshimura 102 (1990) 1035
Nouruzi-Khorasani, A., I.P. Jones, P.S. Dobson, Y. Etem, D.J. Williams, M.G. Astles, C. Ard and G. Coates, A cross-sectional TEM study of MOVPE grown CdHgTe 102 (1990) 819
Nouruzi-Khorasani, A., M.A. Lunn, I.P. Jones, P.S. Dobson, D.J. Williams and M.G. Astles, Surface damage of CdTe by mechanical polishing investigated by cross-sectional TEM 102 (1990) 1069

Oesten, R. and H. Böhm, Flux growth of melilite single crystals 102 (1990) 919
Ohdomari, I., see Ueno 102 (1990) 643
Ohshima, N., see Koide 102 (1990) 690
Okabe, T., see Kitano 102 (1990) 965
Okamoto. A., see Furuhata 102 (1990) 814
Olech, A.Z. and S.A. Hodorowicz, The growth kinetics of urea monocrystals from 1-propanol-aqueous solutions 102 (1990) 562
Ono, H., Axial dislocations in LEC-grown In-doped GaAs crystals 102 (1990) 949
Ori, O., see De Melo 102 (1990) 141
Otoki, Y., see Inada 102 (1990) 915
Owczarek, I. and K. Sangwal, Effect of impurities on the growth of KDP crystals: mechanism of adsorption on (101) faces 102 (1990) 574
Ozasa, K., M. Yuri and H. Matsunami, Temperature dependence of InGaP, InAlP, and AlGaP growth in metalorganic molecular-beam epitaxy 102 (1990) 31

Pak, K., see Tanako 102 (1990) 341
Pamiatnikh, A., see Melikhov 102 (1990) 885
Parat, K.K., N.R. Taskar, I.B. Bhat and S.K. Ghandhi, The influence of accumulation of the Hall-effect in n-type $Hg_{1-x}Cd_xTe$ 102 (1990) 413
Pelleg, J., see Ditchek 102 (1990) 401
Pellegrino, S., see Chen 102 (1990) 477
Pelosi, C., see De Melo 102 (1990) 141
Pénisson, J.-M. and A. Renou, Structure of an isocahedral palladium particle 102 (1990) 585
Perez, M., see Vazquez 102 (1990) 891
Piechotka, M., see Isshiki 102 (1990) 344
Pinchaux, R., see Jedrecy 102 (1990) 293
Pistorius, J.A., see Haisma 102 (1990) 979
Pistorius, J.A., see Haisma 102 (1990) 1014
Pohl, L., see Frese 102 (1990) 290
Poudoulec, A., see Guenais 102 (1990) 925
Poudoulec, A., see Auvray 102 (1990) 939
Prandl, W., see Sonntag 102 (1990) 957
Prasad, P.B.V., Dispersion in crystal growth rates: palmitic acid–xylene system 102 (1990) 569
Pratte, J.M. and J.E. Hart, Endwall driven, low Prandtl number convection in a shallow rectangular cavity 102 (1990) 54

Ramana, M.S.V., see Desai 102 (1990) 191
Rashkovich, L.N., see Chernov 102 (1990) 793
Regel, G.K., see Frese 102 (1990) 290
Regreny, A., see Auvray 102 (1990) 939
Ren Zhifeng, J.G. Wen, Jiang Yandao and Guan Weiyan, Growth and characterization of 2201 single crystals in Bi-based system 102 (1990) 349
Renaud, M., see Bruines 102 (1990) 769
Renou, A., see Pénisson 102 (1990) 585
Ristić, R.I., J.N. Sherwood and T. Shripathi, Strain variation in the {100} growth sectors of potash alum single crystals and its relationship to growth rate dispersion 102 (1990) 245

Robert, F., see Gouzerh 102 (1990) 1059
Roberts, K.J., J.N. Sherwood and A. Stewart, The nucleation of n-eicosane crystals from solution in n-dodecane in the presence of homologous impurities 102 (1990) 419
Rodriguez, T., see Sanz-Maudes 102 (1990) 1065
Roksnoer, P.J., see Haisma 102 (1990) 1014
Ropars, G., see Caulet 102 (1990) 309
Route, R.K., see Lu 102 (1990) 807
Roy, S.N., H. Xu, S. Tan, B. Hinz and I. Müller, Growth of CuZnAl and CuAlNi single crystals with shape memory martensites 102 (1990) 1061
Russell, G.J., see Loginov 102 (1990) 827

Sabharwal, S.C., see Gadkari 102 (1990) 685
Sadler, D.E., see Davey 102 (1990) 97
Sakonjyu, M., see Hibiya 102 (1990) 862
Sangrador, J., see Sanz-Maudes 102 (1990) 1065
Sangwal, K., see Owczarek 102 (1990) 574
Sanz-Maudes, J., J. Sangrador and T. Rodriguez, Numerical description of the phase diagram of the Hg–Cd–Te system in the Te-rich corner 102 (1990) 1065
Sarma, R.L., Electrocrystallization of copper in the presence of 2-thiouracil – a comparative study of the substrate orientation effects 102 (1990) 542
Sasaki, Y., see Shibata 102 (1990) 557
Satoh, T., see Hibiya 102 (1990) 862
Satunkin, G.A. and A.G. Leonov, Weighing control of the automatic crystallization process from the melt 102 (1990) 592
Sauvage-Simkin, M., see Jedrecy 102 (1990) 293
Schlom, D.G., A.F. Marshall, J.T. Sizemore, Z.J. Chen, J.N. Eckstein, I. Bozovic, K.E. von Dessonneck, J.S. Harris, Jr. and J.C. Bravman, Molecular beam epitaxial growth of layered Bi–Sr–Ca–Cu–O compounds 102 (1990) 361
Scholz, F., see Molassioti 102 (1990) 974
Schwab, C., see Wu 102 (1990) 701
Schwartz, G.P., G.J. Gualtieri and W.A. Sunder, Molecular beam epitaxy growth and characterization of GaSb/AlSb strained-layer superlattices on nonvicinal (001) and 111(B) GaSb substrates 102 (1990) 147
Sekimoto, T., see Kubota 102 (1990) 434
Shao, Z.S., see Zhang 102 (1990) 581
Sherwood, J.N., see Ristić 102 (1990) 245
Sherwood, J.N., see Roberts 102 (1990) 419
Shiau, J.-J., see Lu 102 (1990) 807
Shibata, M., Y. Sasaki, T. Inada and S. Kuma, Observation of edge-facets in ⟨100⟩ InP crystals grown by LEC method 102 (1990) 557
Shimizu, K., see Kubota 102 (1990) 434
Shive, L., see Fraundorf 102 (1990) 157
Shripathi, T., see Ristić 102 (1990) 245
Silveira, J.P., see Vazquez 102 (1990) 891
Singh, K.D., see Gadkari 102 (1990) 685
Sizemore, J.T., see Schlom 102 (1990) 361
Smet, F., see Van Enckevort 102 (1990) 314
Snyder, D., see Bevan 102 (1990) 785
Söhnel, O., see Bennema 102 (1990) 547
Sonntag, R., D. Hohlwein, K. Herz, W. Prandl, G. Eckold and Th. Wolf, Characterization of large $YBa_2Cu_3O_{7-x}$ single crystals by neutron diffraction 102 (1990) 957
Stewart, A., see Roberts 102 (1990) 419
Stringfellow, G.B., see Larsen 102 (1990) 103
Stringfellow, G.B., see Li 102 (1990) 117
Stringfellow, G.B., see Larsen 102 (1990) 126
Su Genbo, see Huang 102 (1990) 762
Sunagawa, I., see Maiwa 102 (1990) 43
Sunder, W.A., see Laudise 102 (1990) 21
Sunder, W.A., see Schwartz 102 (1990) 147
Sunder, W.A., see Laudise 102 (1990) 427
Suzuki, J., see Yoshida 102 (1990) 696
Suzuki, K., see Ueno 102 (1990) 643
Szekely, J., see Dilawari 102 (1990) 635

Takekawa, S., see Iida 102 (1990) 398
Takena, M., see Terashima 102 (1990) 387
Taki, S., see Yoshimura 102 (1990) 1035
Talik, E., J. Szade, J. Heimann, A. Winiarski, A. Winiarska, K. Majewska and A. Chełkowski, Growth of $Fe_{3-x}V_xAl$ 102 (1990) 187
Tan, S., see Roy 102 (1990) 1061
Tanako, Y., Y. Kanaya, T. Torihata, K. Pak and H. Yonezu, Growth modes and reduction of hillock density in migration enhanced epitaxy of GaAs(111)B 102 (1990) 341
Tang, X., see Keizer 102 (1990) 667
Tang, Y.S. and Zhang Jingping, Recrystallization of erbium implantation-induced amorphous silicon on insulator by rapid thermal annealing 102 (1990) 681
Tao, X.T., see Zhang 102 (1990) 581
Taskar, N.R., see Parat 102 (1990) 413
Terashima, K., M. Kawachi and M. Takena, Growth of ZnSe crystals by nonstoichiometric annealing 102 (1990) 387
Thompson, N., see Loginov 102 (1990) 827
Torihata, T., see Tanako 102 (1990) 341
Trah, H.-P., Liquid phase epitaxy in the ternary system Si–Ge–Bi 102 (1990) 175
Tsukamoto, K., see Maiwa 102 (1990) 43

Ueno, T., K. Suzuki, Y. Kunii and I. Ohdomari, Mechanism of dislocation formation during vertical solid phase epitaxy 102 (1990) 643
Ungar, L.H., see Kelly 102 (1990) 658

Van der Eerden, J.P., see Witkamp 102 (1990) 281
Van Enckevort, W.J.P. and F. Smet, Optical characterization of crystal dislocations: the case of bismuth germanate 102 (1990) 314

Van Meerten, R.Z.C., see Keizer 102 (1990) 667
Van Rosmalen, G.M., see Witkamp 102 (1990) 281
Van Sark, W.G.J.H.M., J. van Suchtelen, J.E.M. Hogenkamp, M.H.J.M. de Croon, R.A. Velthuis and L.J. Giling, 102 (1990) 1
Van Suchtelen, J., see Van Sark 102 (1990) 1
Vazquez, M., J.P. Silveira, L. Gonzalez, M. Perez, G. Armelles, J.L. De Miguel and F. Briones, Atomic layer molecular beam epitaxy of InAs/AlAs heterostructures 102 (1990) 891
Vekilov, P.G., Yu.G. Kuznetzov and A.A. Chernov, Dissolution morphology and kinetics of (101) ADP face; mild etching of possible surface defects 102 (1990) 706
Velthuis, R.A., see Van Sark 102 (1990) 1
Venerus, D.C., Analysis of finite length dynamics in Czochralski crystal growth 102 (1990) 376
Verbeeck, R.M.H. and J.A.H. Devenyns, The effect of the solution Ca/P ratio on the kinetics of dissolution of octacalcium phosphate at constant pH 102 (1990) 647
Viale, D., G. Weber and B. Gillot, Growth of Cu_3Si from CuCl vapor deposition on Si(100) oriented wafers 102 (1990) 269
Visser, E.P., C.A.M. Govers and L.J. Giling, Measurement of gas-switching related diffusion phenomena in horizontal MOCVD reactors using biacetyl luminescence 102 (1990) 529
Voiticek, A., see Clemens 102 (1990) 933
Völkel, E., see Mateika 102 (1990) 994
Von Dessonneck, K.E., see Schlom 102 (1990) 361

Wang, G.Y., see Wu 102 (1990) 701
Wang, J.R., see Wu 102 (1990) 701
Wang, Guofu and Zundu Luo, $Nd^{3+}:KY(WO_4)_2$ crystal growth and X-ray diffraction 102 (1990) 765
Wang Qiwei and Jia Shouquan, Theoretical estimation of the crystal growth driving force during slow cooling 102 (1990) 678
Watanabe, H., see Kakimoto 102 (1990) 16
Weber, G., see Viale 102 (1990) 269
Wen, J.G., see Ren 102 (1990) 349
Wheeler, A.A., Four test problems for the numerical simulation of flow in Czochralski crystal growth 102 (1990) 691
Williams, D.J., see Nouruzi-Khorasani 102 (1990) 819
Williams, D.J., see Nouruzi-Khorasani 102 (1990) 1069
Williams, L.J., see Davey 102 (1990) 97
Witkamp, G.J., J.P. van der Eerden and G.M. van Rosmalen, Growth of gypsum. I. Kinetics 102 (1990) 281
Witt, A.F., see Laudise 102 (1990) 21
Wolf, Th., see Sonntag 102 (1990) 957
Woods, J., see Loginov 102 (1990) 827
Wu, J., P.G. Mo, G.Y. Wang, S. Benakki, E. Christoffel, A. Goltzene, C. Schwab, J.R. Wang and C.H. Lee, Influence of In-doping on dislocations in liquid encapsulated Czochralski (LEC) grown gallium arsenide 102 (1990) 701
Wu, P.T., see Lin 102 (1990) 354
Wynblatt, P., J.J. Métois and J.C. Heyraud, Modeling the growth of dendrite-like gold islands on graphite substrates 102 (1990) 618

Xu, D., see Zhang 102 (1990) 581
Xu, H., see Roy 102 (1990) 1061

Yamaguchi, H., see Kobayashi 102 (1990) 471
Yasuda, Y., see Koide 102 (1990) 690
Yokota, T., see Yoshimura 102 (1990) 1035
Yonezu, H., see Tanako 102 (1990) 341
Yoo, H.J., see Caneau 102 (1990) 491
Yoshida, S., J. Suzuki, M. Nakayama and T. Kikuta, High quality SI-InP bulk crystal growth by horizontal gradient freeze method under controlled phosphorus vapor pressure 102 (1990) 696
Yoshimura, J., S. Taki, K. Nonaka, M. Kobayashi and T. Yokota, Etch figures of berlinite by HF, NH_4HF_2, H_3PO_4 and NaOH solutions 102 (1990) 1035
Yuan, D.R., see Zhang 102 (1990) 581
Yuri, M., see Ozasa 102 (1990) 31

Zaima, S., see Koide 102 (1990) 690
Zaitseva, N.P., see Chernov 102 (1990) 793
Zhang, N., M.H. Jiang, D.R. Yuan, D. Xu, X.T. Tao and Z.S. Shao, The quality and performance of the organometallic complex nonlinear optical material tri-allylthiourea cadmium chloride (ATCC) 102 (1990) 581
Zundelevich, Y. and R. Glaser, Activity of growth centers during spiral growth of KDP in aqueous solution: a statistical approach 102 (1990) 69

Journal of Crystal Growth 102 (1990) 1082–1085
North-Holland

SUBJECT INDEX

Accelerated-crucible rotation technique 848
Additives 801
Adducts 290, 775
Adsorption 233, 303, 542
Alloys 187, 481, 725, 1061
Alum
– potash 245
Aluminum
– antimonide 147
– arsenide 717, 891
– gallium arsenide 1, 814
– gallium phosphide 31
– organic 31, 814
– oxide 505
– oxide–silicon oxide 908
– phosphate 305
– phosphide 31
Ammonium
– dihydrogen phosphate 706, 793
Apparatus
– for melt growth
– – by Bridgman–Stockbarger method
– – – of copper alloys 1061
– – by Czochralski method
– – – using vibrational stirring
– – – – of cadmium telluride 807
– – by gradient freeze method
– – – of indium phosphide 696
– for solution growth
– – by low temperature method
– – – of ammonium dihydrogen phosphate 706
– – – of barium carbonate 434
– – – of barium nitrate 43
– – – or organic crystals 801
– for thin film growth
– – by metalorganic molecular beam epitaxy
– – – of aluminum gallium arsenide 814
– – – of gallium arsenide 814
– – by vapor phase epitaxy
– – – through metalorganic chemical vapor deposition
– – – – using barrel-type reactor
– – – – – of gallium arsenide 635
– – – – using pulse reactor
– – – – – of aluminum gallium arsenide 1
– – – – – of gallium arsenide 1
– for vapor growth
– – by evaporation and condensation
– – – of α-mercuric iodide 344
– for miscellaneous purposes
– – biacetyl luminescence for simulation of MOCVD growth 529
– in situ observation of ice crystals by laser scattering tomography 167
– numerical simulation of flow in Czochralski growth 691
Arsenic
– organic 117, 183

Barium
– carbonate 434
– fluoride 303
– nitrate 43
Berlinite 1035
Biomineralization 262
Bismuth 725
– germanate 314
– strontium calcium cuprate 349, 354, 361, 685
Boron 899
Boundary layer control 69, 562, 706

Cadmium
– chloride–organic complex 581
– mercury telluride 413, 785, 819, 848, 1065
– telluride 807, 1069
Calcium
– carbonate 262
– phosphate 609, 647
– sulphate dihydrate 281
– tartrate 501
Characterization methods
– by absorption spectroscopy 915
– by Auger electron spectroscopy
– by chemical analysis 919
– by differential thermal analysis 765
– by electrical methods 21, 183, 249, 290, 354, 393, 413, 477, 501, 685, 691, 769, 785, 807, 814, 877, 915, 974, 1059
– by electron diffraction 157, 349
– by electron microscopy 21, 157, 175, 255, 262, 269, 281, 309, 349, 401, 434, 491, 574, 585, 618, 643, 685, 819, 827, 862, 899, 908, 925, 939, 949, 965, 1014, 1061, 1069
– by electron probe microanalysis 862, 1059
– by emission 529
– by ferroelectricity 501
– by interferometry 43, 706
– by laser scattering tomography 167
– by magnetic properties 1059
– by mass spectrometry 775
– by neutron diffraction 957

- by optical microscopy 31, 43, 137, 147, 175, 191, 249, 262, 314, 329, 387, 398, 427, 542, 557, 706, 717, 762, 765, 793, 819, 827, 857, 877, 885, 1035, 1061
- by particle size distribution analysis 269, 434
- by photoluminescence 137, 147, 290, 477, 769, 814
- by Raman spectroscopy 147, 869, 891
- by reflection high energy electron diffraction 31, 293, 309, 341, 361, 690, 891, 933
- by Rutherford back scattering 309, 361, 681
- by secondary ion mass spectrometry 249, 393, 974
- by thermal methods 725
- by X-ray methods 16, 21, 157, 175, 187, 245, 255, 269, 293, 309, 349, 354, 361, 398, 401, 685, 701, 765, 785, 807, 827, 877, 891, 899, 933, 939, 965, 979, 994, 1059

Chirality 97
Clathrates 255
Computer simulation 69, 618, 658, 691, 1043
Constitutional supercooling 481, 848
Convection 16, 54, 197, 214, 223, 401, 441, 481, 505, 562, 691, 706, 807, 848, 1043
Copper 542
- alloys 1061
- aluminum nickel 1061
- silicide 269
- zinc aluminum 1061

Dendritic growth 618, 857, 885
Devices 1, 309, 491
Dextrose 869
Diffusional control 1, 197, 303, 529, 562, 691, 706, 725, 801, 908, 974
Dislocations 43, 69, 245, 314, 643, 701, 706, 769, 793, 819, 827, 877, 949, 1035, 1069
Dissolution 255, 303, 647, 706
Distribution coefficient 21, 419, 725, 807, 848, 994
Dopants 183, 249, 349, 393, 419, 658, 667, 827, 877, 949, 974

Erbium
- phosphide arsenide 309

Etching
- chemical 175, 314, 398, 491, 701, 877, 1035
- melt back 491
- thermal 167, 643, 706

Eutectic growth 401

Fatty acids 569
Four–six (IV–VI) compounds 933
Fractals 618

Gallium
- aluminum arsenide 939
- antimonide 147
- arsenide 1, 103, 117, 126, 183, 290, 293, 309, 341, 441, 471, 529, 635, 667, 701, 717, 814, 877, 915, 939, 949
- indium arsenide 775
- indium arsenide phosphide 491
- organic 31, 103, 126, 183, 290, 441, 667, 814

Garnets 994, 1014
Germanium 690
- gallium 725

Gold 618
Grain boundary 314, 387
Gypsum 281

Heat flow control 441, 725, 743
Heterojunction 293, 529, 891
Hydrodynamics 529, 743

Ice 167
Impurity 69, 97, 183, 214, 223, 255, 387, 393, 419, 447, 562, 574, 658, 706, 725, 857, 877
Inclusions 793, 857
Indium
- aluminum phosphide 31
- antimonide 725
- arsenide 891
- gallium arsenide 447
- gallium phosphide 31
- organic 31, 393, 775
- phosphide 249, 393, 557, 696, 769, 974

Interface 69, 309, 481, 505, 529, 547, 557, 658, 706, 725, 841, 857, 891, 925, 1043
Iron
- vanadium aluminum alloy 187

Kinetics
- of dissolution 303, 647, 706
- of growth 1, 31, 43, 69, 103, 117, 126, 137, 269, 281, 344, 393, 427, 471, 562, 569, 574, 618, 629, 635, 658, 681, 690, 706, 717, 769, 775, 801, 814, 857, 885, 891, 939, 965
- of interface control 43, 69
- of nucleation 225, 269, 419, 434, 609, 629, 965
- of spiral cooperation 69

Lasers 249
Lattice mismatch 293, 309, 491, 785, 979, 1014
Lead
- hydrogen phosphate 191
- manganese telluride 933
- telluride 933
- yttrium barium cuprate 862

Lutetium
- ferrite 398
- iron cobaltite 398

Mathematical model 103, 117, 126, 141, 376, 441, 505, 592, 635, 725, 743, 775
Melilite 919
Melt growth technique
- by Bridgman–Stockbarger method
  - of cadmium telluride 807
  - of copper alloys 1061
  - of gallium arsenide 877
  - of iron vanadium aluminum alloy 197

– – of mercury cadmium telluride 848
– – theory of 197
– by Czochralski method
– – of gallium arsenide 701, 915, 949
– – of garnets 994
– – of indium phosphide 557
– – of iron vanadium aluminum alloy 187
– – of oxides 505
– – of platinum antimonide 21
– – of platinum manganese antimonide 21
– – of silicon 16, 157
– – of silicon tantalum disilicide eutectic 401
– – theory of 376, 505, 592, 691
– by floating zone method
– – of lutetium ferrite 398
– – of lutetium iron cobaltite 398
– – of molybdenum 214
– – of silicon 1043
– – of yttrium iron magnesium oxide 398
– by gradient freeze method
– – of indium phosphide 696
– by uniaxial solidification
– – of alloys 725
– – of silicon 658
– – theory of 481, 658
– by zone melting
– – of molybdenum 223
– – of niobium 223
Mercury
– cadmium telluride 413, 785, 819, 848, 1065
– (II) iodide, α 344
Metal
– oxides 505
Microgravity 1043
Molecular dynamics 658
Molybdenum 214, 223
Monte Carlo method 69, 618, 658
Morphological stability 233, 481
Morphology of growth 1, 43, 137, 147, 157, 175, 233, 255, 262, 269, 281, 290, 309, 329, 341, 344, 401, 542, 557, 685, 769, 801, 819, 857, 869, 885, 899, 925, 965, 994
Mullite 908

Nickel
– complex clathrate 255
– gallium 925
Niobium 223
Nonlinear optics 581
Nucleation 191, 255, 262, 269, 419, 574, 609, 629, 793, 741, 869, 908, 965
Numbers
– Biot 214, 376, 1043
– Grashof 54, 197, 441, 505, 529, 691, 743
– Lewis 197
– Marangoni 214, 223, 1043
– Peclet 197, 743, 1043
– Prandtl 16, 54, 197, 214, 223, 1043
– Rayleigh 197
– Reynolds 505, 529
– Schmidt 197, 214

Optical isomers 97
Organic crystals 97, 419, 562, 569, 762, 801, 857, 885
Oxides
– metallic 505

Palladium 585
Perfection of crystals 43, 141, 167, 187, 191, 245, 314, 349, 387, 401, 427, 569, 581, 585, 643, 685, 706, 785, 793, 807, 819, 827, 848, 857, 877, 949, 994, 1069
Periodic bond chain theory 329
Phase diagrams 141, 175, 427, 862, 915, 1065
Phenomenological theory 69, 562
Platinum 629
– antimonide 21
– manganese antimonide 21
Polymorphism/polytypism 255
Potassium
– aluminum sulphate 245
– dihydrogen phosphate 69, 574, 793
– titanyl phosphate 329, 427
– yttrium tungstate 765
Precursor 31, 103, 117, 126, 183, 290, 775, 785
Purification of materials 97, 255, 419, 477

Quantum wells/size effects 147, 939

Salts
– inorganic 547
Segregation 848
Silicon 16, 157, 233, 376, 643, 658, 681, 1043
– germanide 175
– tantalum disilicide eutectic 401
Solid growth technique
– by recrystallization
– – of calcium carbonate 262
– – of silicon 643, 681
– – of zinc selenide 387
Solubility 762
Solution growth technique
– by electrocrystallization
– – of copper 542
– – of lead hydrogen phosphate 191
– by flux method
– – of bismuth strontium calcium cuprate 349, 685
– – of melilite 919
– – of nickel complex clathrate 255
– – of potassium titanyl phosphate 329
– – of potassium yttrium tungstate 765
– – of yttrium barium cuprate 862, 1059
– – theory of 678
– by gel method
– – of calcium tartrate 501
– – of lead hydrogen phosphate 191
– by hydrothermal growth
– – of berlinite 1035

– – of potassium titanyl phosphate 427
– by low temperature method
– – of ammonium dihydrogen phosphate 706, 793
– – of barium carbonate 434
– – of barium fluoride 303
– – of barium nitrate 43
– – of calcium phosphates 609, 647
– – of dextrose 869
– – of fatty acids 569
– – of gypsum 281
– – of inorganic salts 547
– – of organic crystals 97, 801
– – of organo cadmium chloride complex 581
– – of potassium aluminum sulphate 245
– – of potassium dihydrogen phosphate 69, 574, 793
– – of urea 562, 762
– – theory of 69, 547
Statistical mechanics, molecular theory 233
Stefan problem or moving boundary problem 376, 505, 725, 1043
Step 43, 69, 233, 629, 706
Strain 69, 147, 187, 245, 314, 585, 706, 793, 891
Superconductivity 354, 361, 685, 957, 1059
– bulk 685, 957, 1059
– characterization 354, 361, 685, 957, 1059
– crystal chemistry 354, 361, 685, 957, 1059
– high T_c 354, 361, 685, 957, 1059
– stoichiometry 361, 685, 957, 1059
– thin films 354, 361
Supercooling, supersaturation 249, 255, 344, 427, 562, 574, 706, 793, 801, 857, 885
Superlattices 147, 529, 891, 939, 974
Surface energy, determination of 43, 69, 419, 547, 706, 841
Surface processes 233, 393, 629, 643, 706, 717
Surface structure 706, 1069

Thermodynamics 141, 183, 233, 547, 574, 667, 801, 841, 1065
Thermophoresis 743
Thin film growth
– by atomic layer molecular beam epitaxy
– – of aluminum arsenide 891
– – of indium arsenide 891
– by liquid phase epitaxy
– – of gallium indium arsenide phosphide 491
– – of indium gallium arsenide 477
– – of indium phosphide 249
– – of mercury cadmium telluride 1065
– – of silicon germanide 175
– by metalorganic molecular beam epitaxy
– – of aluminum gallium arsenide 814
– – of gallium arsenide 814
– – of three–five (III–V) compounds 31
– by molecular beam epitaxy
– – of aluminum antimonide 147
– – of bismuth strontium calcium cuprate 361
– – of erbium phosphide arsenide 309
– – of four–six (IV–VI) compounds 933
– – of gallium aluminum arsenide 939
– – of gallium antimonide 147
– – of gallium arsenide 293, 309, 341, 939
– – of germanium 690
– – of nickel gallium 925
– by vapor phase epitaxy
– – through chemical vapor deposition
– – – of boron 899
– – – of copper silicide 269
– – – of silicon 233, 643
– – – of three–five (III–V) compounds 1014
– – – theory of 743
– – through evaporation and condensation
– – – of bismuth strontium calcium cuprate 354
– – – of mullite 908
– – – of platinum 629
– – through multilayer interdiffusion process
– – – of mercury cadmium telluride 819
– – through metalorganic chemical vapor deposition
– – – of aluminum arsenide 717
– – – of aluminum gallium arsenide 1
– – – of gallium arsenide 1, 103, 117, 183, 290, 441, 529, 635, 667, 717
– – – of gallium indium arsenide 775
– – – of indium phosphide 393, 974
– – – of mercury cadmium telluride 413, 785
– – – simulation of 529
– – – theory of 441
Three–five (III–V) compounds 31, 1014
Tin
– bismuth 725
Transistor 491
Twinning 557, 585, 681, 696, 785, 819, 957

Uniformity of growth 1, 775, 1061
Urea 562, 762

Vapor growth technique
– by chemical transport
– – of gallium arsenide 471
– – of zinc oxide 137, 965
– by evaporation and condensation
– – of mercury (II) iodide, α 344
– – of zinc selenide 827
– – of zinc sulphide 827

Whisker growth
– of boron 899
– of zinc oxide 965

Ytterbium
– iron magnesium oxide 398
Yttrium
– barium cuprate 862, 957, 1059

Zinc
– oxide 137, 965
– selenide 387, 827
– sulphide 827